Hyung Koun Cho

List of Publications by Year in Descending Order

312 papers	5,288 citations	36 h-index	56 g-index
331 ext. papers	5,813 ext. citations	3.8 avg, IF	5.61 L-index

#	Paper	IF	Citations
312	Design of hydrangea-type Co/Mo bimetal MOFs and MOF-derived Co/Mo2C embedded carbon composites for highly efficient oxygen evolution reaction. *Chemical Engineering Journal*, **2022**, 435, 134815	14.7	5
311	A synergistic strategy to remove hazardous water pollutants by mimicking burdock flower morphology structures of iron oxide phases. *Chemosphere*, **2022**, 286, 131789	8.4	
310	Atomic-scale platinum deposition on photocathodes by multiple redox cycles under illumination for enhanced solar-to-hydrogen energy conversion. *Journal of Power Sources*, **2022**, 533, 231410	8.9	1
309	Area-Selective Chemical Doping on Solution-Processed MoS Thin-Film for Multi-Valued Logic Gates. *Nano Letters*, **2021**,	11.5	5
308	Optimal n-Type Al-Doped ZnO Overlayers for Charge Transport Enhancement in p-Type CuO Photocathodes. *Micromachines*, **2021**, 12,	3.3	1
307	Compositional Engineering of Hf-Doped InZnSnO Films for High-Performance and Stability Amorphous Oxide Semiconductor Thin Film Transistors. *Advanced Electronic Materials*, **2021**, 7, 2001216	6.4	8
306	-like FeOOH Nanoswords Activated by Ni Foam and Encapsulated by rGO toward High Current Densities, Durability, and Efficient Oxygen Evolution. *ACS Applied Materials & Interfaces*, **2021**, 13, 18772-18783	9.5	2
305	High-Performance Non-Volatile InGaZnO Based Flash Memory Device Embedded with a Monolayer Au Nanoparticles. *Nanomaterials*, **2021**, 11,	5.4	5
304	Bundle-Type Columnar Cu2O Photoabsorbers with Vertical Grain Boundaries Fabricated Using Instant Strike-Processed Metallic Seeds and Their Enhanced Photoelectrochemical Efficiency. *ACS Sustainable Chemistry and Engineering*, **2021**, 9, 6390-6399	8.3	1
303	Interleaved biphasic p- blended copper indium selenide photoelectrode and its application in pulse-driven photoelectrochemical water splitting. *Applied Catalysis B: Environmental*, **2021**, 285, 119839	21.8	9
302	Significantly enhanced chemical stability in interface-controlled Cu2+Se-reduced graphene oxide composites and related thermoelectric performances. *Journal of the European Ceramic Society*, **2021**, 41, 459-465	6	4
301	Energy Transfer-Induced Photoelectrochemical Improvement from Porous Zeolitic Imidazolate Framework-Decorated BiVO Photoelectrodes.. *Small Methods*, **2021**, 5, e2000753	12.8	6
300	Rapid thermal annealing effect of transparent ITO source and drain electrode for transparent thin film transistors. *Ceramics International*, **2021**, 47, 3149-3158	5.1	11
299	Progressive NO2 Sensors with Rapid Alarm and Persistent Memory-Type Responses for Wide-Range Sensing Using Antimony Triselenide Nanoflakes. *Advanced Functional Materials*, **2021**, 31, 2102439	15.6	4
298	Toward Simultaneous Achievement of Outstanding Durability and Photoelectrochemical Reaction in Cu2O Photocathodes via Electrochemically Designed Resistive Switching. *Advanced Energy Materials*, **2021**, 11, 2101905	21.8	4
297	Atomically tunable photo-assisted electrochemical oxidation process design for the decoration of ultimate-thin CuO on Cu2O photocathodes and their enhanced photoelectrochemical performances. *Journal of Materials Chemistry A*, **2020**, 8, 21744-21755	13	10
296	Smart Bifunctional Sb Se Nanorods for Integrated Water Purification: Insoluble Liquid Separation and Photoelectrochemical Degradation. *ChemSusChem*, **2020**, 13, 3017-3027	8.3	3

295	Tailoring the magnetic hyperthermia performances of gram-bean-extract-mediated highly disperse MFe2O4 (M = Fe, Ni, Mn) nanoferrites. *Ceramics International*, **2020**, 46, 24290-24301	5.1	7
294	Formation of five-fold twinning electron diffraction pattern and twinning bands in bulk CuIn3Se5 via hot deformation. *Materials Letters*, **2020**, 276, 128251	3.3	
293	ZnO decorated flexible and strong graphene fibers for sensing NO2 and H2S at room temperature. *Sensors and Actuators B: Chemical*, **2020**, 308, 127690	8.5	43
292	Bifunctional reusable Co0.5Ni0.5Fe2O4 nanoparticle-grafted carbon nanotubes for aqueous dye removal from contaminated water. *Catalysis Science and Technology*, **2020**, 10, 6188-6197	5.5	2
291	Toward ultraviolet solution processed ZrOx/IZO transistors with top-gate and dual-gate operation: Selection of solvents, precursors, stabilizers, and additive elements. *Journal of Alloys and Compounds*, **2020**, 847, 156431	5.7	4
290	High-Intensity Ultrasound-Assisted Low-Temperature Formulation of Lanthanum Zirconium Oxide Nanodispersion for Thin-Film Transistors. *ACS Applied Materials & Interfaces*, **2020**, 12, 44926-44933	9.5	5
289	Controlled nanostructured morphology of BiVO4 photoanodes for efficient on-demand catalysis in solar water-splitting and sustainable water-treatment. *Applied Surface Science*, **2020**, 514, 146075	6.7	13
288	Multi-spectral gate-triggered heterogeneous photonic neuro-transistors for power-efficient brain-inspired neuromorphic computing. *Nano Energy*, **2019**, 66, 104097	17.1	27
287	Electrochemically Assembled CuO Nanoparticles Using Crystallographically Anisotropic Functional Metal Ions and Highly Expeditious Resistive Switching via Nanoparticle Coarsening. *ACS Nano*, **2019**, 13, 5987-5998	16.7	7
286	Enhanced Gas Sensing Performance of Hydrothermal MoS2 Nanosheets by Post-Annealing in Hydrogen Ambient. *Bulletin of the Chemical Society of Japan*, **2019**, 92, 1094-1099	5.1	14
285	Enhanced Gas Sensing Performance of Surface-Activated MoS2 Nanosheets Made by Hydrothermal Method with Excess Sulfur Precursor. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800999	1.6	3
284	Toward Robust Photoelectrochemical Operation of Cuprous Oxide Nanowire Photocathodes Using a Strategically Designed Solution-Processed Titanium Oxide Passivation Coating. *ACS Applied Materials & Interfaces*, **2019**, 11, 14840-14847	9.5	7
283	Bionanoelectronic platform with a lipid bilayer/CVD-grown MoS hybrid. *Biosensors and Bioelectronics*, **2019**, 142, 111512	11.8	4
282	Highly Improved Quasi-Two-Dimensional Oxide Transistors via Non-centrosymmetric Nitrogen Dioxide Treatment, toward Extremely Low Process Temperature and Operant Self-Aligned Coplanar Structure. *ACS Applied Materials & Interfaces*, **2019**, 11, 28397-28406	9.5	0
281	Inactivation of low-temperature-induced numerous defects at the electrode/channel interfaces using ultrathin Al2O3 layers. *Microelectronic Engineering*, **2019**, 216, 111049	2.5	1
280	Optimal synthesis of antimony-doped cuprous oxides for photoelectrochemical applications. *Thin Solid Films*, **2019**, 671, 120-126	2.2	6
279	Compositionally graded SnO2/TiO2 bi-layered compounds with dramatically enhanced charge transport efficiency for self-driven water purification applications. *Journal of Alloys and Compounds*, **2019**, 776, 839-849	5.7	7
278	Toward Adequate Operation of Amorphous Oxide Thin-Film Transistors for Low-Concentration Gas Detection. *ACS Applied Materials & Interfaces*, **2018**, 10, 10185-10193	9.5	34

277	Ultralow Lattice Thermal Conductivity and Significantly Enhanced Near-Room-Temperature Thermoelectric Figure of Merit in □Cu2Se through Suppressed Cu Vacancy Formation by Overstoichiometric Cu Addition. *Chemistry of Materials*, **2018**, 30, 3276-3284	9.6	38
276	Development of extremely low temperature processed oxide thin film transistors via atmospheric steam reforming treatment: Interface, surface, film curing. *Journal of Alloys and Compounds*, **2018**, 744, 23-33	5.7	5
275	Copper indium selenide water splitting photoanodes with artificially designed heterophasic blended structure and their high photoelectrochemical performances. *Nano Energy*, **2018**, 46, 1-10	17.1	5
274	Effects of Precursor Concentration on Dimensional Size, Defect State, and Gas Sensing Performance of MoS2 Sheets Synthesized by Hydrothermal Method. *Physica Status Solidi (A) Applications and Materials Science*, **2018**, 215, 1800079	1.6	5
273	Electrochemical surface charge-inversion from semi-insulating Sb2Se3 photoanodes and abrupt photocurrent generation for water splitting. *Energy and Environmental Science*, **2018**, 11, 2540-2549	35.4	13
272	Comparison of the electronic and thermoelectric properties of three layered phases Bi2Te3, PbBi2Te4 and PbBi4Te7: LEGO thermoelectrics. *AIP Advances*, **2018**, 8, 115213	1.5	5
271	Cuprous/Cupric Heterojunction Photocathodes with Optimal Phase Transition Interface via Preferred Orientation and Precise Oxidation. *ACS Sustainable Chemistry and Engineering*, **2018**, 6, 10364-10373	8.3	16
270	All-Solution-Processed Metal Oxide/Chalcogenide Hybrid Full-Color Phototransistors with Multistacked Functional Layers and Composition-Gradient Heterointerface. *Advanced Optical Materials*, **2018**, 6, 1800196	8.1	7
269	Corrosion Behavior and Metallization of Cu-Based Electrodes Using MoNi Alloy and Multilayer Structure for Back-Channel-Etched Oxide Thin-Film Transistor Circuit Integration. *IEEE Transactions on Electron Devices*, **2017**, 64, 447-454	2.9	8
268	Non-ideal current drop behavior in ultra-thin inorganic a-InGaZnO thin film transistors. *Journal of Materials Science: Materials in Electronics*, **2017**, 28, 8231-8237	2.1	2
267	Electrical and chemical stability engineering of solution-processed indium zinc oxide thin film transistors via a synergistic approach of annealing duration and self-combustion process. *Ceramics International*, **2017**, 43, 8956-8962	5.1	8
266	The pH-dependent corrosion behavior of ternary oxide semiconductors and common metals and its application for solution-processed oxide thin film transistors circuit integration. *Journal of Alloys and Compounds*, **2017**, 714, 572-582	5.7	6
265	Microstructure-dependent thermoelectric properties of polycrystalline InGaO3(ZnO)2 superlattice films. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2017**, 35, 01B126	2.9	5
264	Chemical durability engineering of solution-processed oxide thin films and its application in chemically-robust patterned oxide thin-film transistors. *Journal of Materials Chemistry C*, **2017**, 5, 339-349	7.1	19
263	Environment-stable solar window modules encapsulated with UV-curable transparent resin. *Solar Energy*, **2017**, 158, 528-532	6.8	3
262	Towards environmentally stable solution-processed oxide thin-film transistors: a rare-metal-free oxide-based semiconductor/insulator heterostructure and chemically stable multi-stacking. *Journal of Materials Chemistry C*, **2017**, 5, 10498-10508	7.1	17
261	Dual Role of Sb-Incorporated Buffer Layers for High Efficiency Cuprous Oxide Photocathodic Performance: Remarkably Enhanced Crystallinity and Effective Hole Transport. *ACS Sustainable Chemistry and Engineering*, **2017**, 5, 8213-8221	8.3	11
260	Crystal growth direction-controlled antimony selenide thin film absorbers produced using an electrochemical approach and intermediate thermal treatment. *Solar Energy Materials and Solar Cells*, **2017**, 172, 11-17	6.4	7

259	High photosensitivity and wide operation voltage in two-dimensional CdS nano-crystal layer embedded a-InGaZnO hybrid phototransistors. *Journal of Alloys and Compounds*, **2017**, 725, 891-898	5.7	11
258	Thermoelectric transport properties of tetradymite-type Pb1-Sn Bi2Te4 compounds. *Journal of Alloys and Compounds*, **2017**, 690, 966-970	5.7	3
257	Effects of Cu incorporation as an acceptor on the thermoelectric transport properties of Cu Bi2Te2.7Se0.3 compounds. *Journal of Alloys and Compounds*, **2017**, 696, 213-219	5.7	12
256	An All Oxide-Based Imperceptible Thin-Film Transistor with Humidity Sensing Properties. *Materials*, **2017**, 10,	3.5	13
255	All-Solution Processedn n-ZnO Nanorods/i-CdS/p-Cu2O Diodes Prepared Using Diluted Solution Precursors. *Nanoscience and Nanotechnology Letters*, **2017**, 9, 45-49	0.8	2
254	Binary Oxide p-n Heterojunction Piezoelectric Nanogenerators with an Electrochemically Deposited High p-Type Cu2O Layer. *ACS Applied Materials & Interfaces*, **2016**, 8, 22135-41	9.5	10
253	Low voltage-driven oxide phototransistors with fast recovery, high signal-to-noise ratio, and high responsivity fabricated via a simple defect-generating process. *Scientific Reports*, **2016**, 6, 31991	4.9	33
252	Highly Repeatable and Recoverable Phototransistors Based on Multifunctional Channels of Photoactive CdS, Fast Charge Transporting ZnO, and Chemically Durable Al2O3 Layers. *ACS Applied Materials & Interfaces*, **2016**, 8, 15518-23	9.5	8
251	Chemically robust solution-processed indium zinc oxide thin film transistors fabricated by back channel wet-etched Mo electrodes. *RSC Advances*, **2016**, 6, 53310-53318	3.7	10
250	Extremely Thin Al2O3 Surface-Passivated Nanocrystalline ZnO Thin-Film Transistors Designed for Low Process Temperature. *Journal of the American Ceramic Society*, **2016**, 99, 1305-1310	3.8	6
249	A combinatorial approach to solution-processed InGaO3(ZnO)m superlattice films: growth mechanisms and their thermoelectric properties. *CrystEngComm*, **2016**, 18, 807-815	3.3	4
248	Carrier confinement effect-driven channel design and achievement of robust electrical/photostability and high mobility in oxide thin-film transistors. *Journal of Materials Chemistry C*, **2016**, 4, 727-735	7.1	10
247	Expedient floating process for ultra-thin InGaZnO thin-film-transistors and their high bending performance. *RSC Advances*, **2016**, 6, 63418-63424	3.7	9
246	Periodically pulsed wet annealing approach for low-temperature processable amorphous InGaZnO thin film transistors with high electrical performance and ultrathin thickness. *Scientific Reports*, **2016**, 6, 26287	4.9	12
245	Composition-dependent charge transport and temperature-dependent density of state effective mass interpreted by temperature-normalized Pisarenko plot in Bi2SbxTe3 compounds. *APL Materials*, **2016**, 4, 104812	5.7	10
244	Effects of top-layer thickness on electrical performance and stability in VZTO/ZTO bi-layer thin-film transistors. *Journal of Alloys and Compounds*, **2016**, 672, 449-456	5.7	3
243	Electrodeposition of p-type cuprous oxide layers on n-type zinc oxide layers with different electrical resistivities. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2015**, 33, 02B104	1.3	3
242	Enhancement of the Electrical Performance of Electrodepositedn-Type ZnO Nanorods by Antimony Doping. *Journal of the Electrochemical Society*, **2015**, 162, D350-D353	3.9	

241	Single phase tin sulfide films prepared by one-bath electrodeposition. *Journal of Materials Science: Materials in Electronics*, **2015**, 26, 8609-8615	2.1	2
240	Liquid-solid spinodal decomposition mediated synthesis of Sb_2Se_3 nanowires and their photoelectric behavior. *Nanoscale*, **2015**, 7, 12913-20	7.7	30
239	Dual electrical behavior of multivalent metal cation-based oxide and its application to thin-film transistors with high mobility and excellent photobias stability. *ACS Applied Materials & Interfaces*, **2015**, 7, 6118-24	9.5	20
238	Bi-layer channel structure-based oxide thin-film transistors consisting of ZnO and Al-doped ZnO with different Al compositions and stacking sequences. *Electronic Materials Letters*, **2015**, 11, 198-205	2.9	29
237	Investigation of the photoelectrochemical properties for typical ZnO nanostructures grown by using chemical vapor transport. *Journal of the Korean Physical Society*, **2015**, 66, 832-838	0.6	2
236	Effect of topographical control by a micro-molding process on the activity of human Mesenchymal Stem Cells on alumina ceramics. *Biomaterials Research*, **2015**, 19, 23	16.8	8
235	Low-Temperature Processable High-Performance Electrochemically Deposited p-Type Cuprous Oxides Achieved by Incorporating a Small Amount of Antimony. *Advanced Functional Materials*, **2015**, 25, 5214-5221	15.6	18
234	Enhanced oxygen reduction and evolution by in situ decoration of hematite nanoparticles on carbon nanotube cathodes for high-capacity nonaqueous lithium–oxygen batteries. *Journal of Materials Chemistry A*, **2015**, 3, 13767-13775	13	30
233	Optimization of Synthesis Conditions of Na0.75CoO2 for High Thermoelectric Performance. *Journal of Electronic Materials*, **2015**, 44, 1408-1412	1.9	3
232	Effect of post-annealing temperatures on thin-film transistors with ZnO/Al2O3 superlattice channels. *Thin Solid Films*, **2015**, 584, 336-340	2.2	23
231	Photoelectrochemical water splitting properties of hydrothermally-grown ZnO nanorods with controlled diameters. *Electronic Materials Letters*, **2015**, 11, 65-72	2.9	23
230	Role of ultrathin Al2O3 layer in organic/inorganic hybrid gate dielectrics for flexibility improvement of InGaZnO thin film transistors. *Organic Electronics*, **2014**, 15, 1458-1464	3.5	32
229	Enhancement of Electrical Stability in Oxide Thin-Film Transistors Using Multilayer Channels Grown by Atomic Layer Deposition. *IEEE Transactions on Electron Devices*, **2014**, 61, 73-78	2.9	47
228	Non-toxic selenization using thermal annealing for CuGa/In bi-layer precursors deposited by sputtering. *Journal of Materials Science: Materials in Electronics*, **2014**, 25, 3492-3497	2.1	1
227	All oxide ultraviolet photodetectors based on a p-Cu2O film/n-ZnO heterostructure nanowires. *Thin Solid Films*, **2014**, 570, 282-287	2.2	17
226	Artificially Controlled Two-Step Electrodeposition of Cu and Cu/In Metal Precursors with Improved Surface Roughness for Solar Applications. *Journal of the Electrochemical Society*, **2014**, 161, D447-D452	3.9	6
225	Design of step composition gradient thin film transistor channel layers grown by atomic layer deposition. *Applied Physics Letters*, **2014**, 105, 223513	3.4	12
224	Microstructural characteristics of tin oxide-based thin films on (0001) Al2O3 substrates: effects of substrate temperature and RF power during co-sputtering. *Journal of Nanoscience and Nanotechnology*, **2014**, 14, 8908-14	1.3	3

223	Double-layer channel structure based ZnO thin-film transistor grown by atomic layer deposition. *Physica Status Solidi - Rapid Research Letters*, **2014**, 8, 328-331	2.5	16
222	Anomalous tin chemical bonding in indium-zinc-tin oxide films and their thin film transistor performance. *Journal Physics D: Applied Physics*, **2014**, 47, 485101	3	21
221	Effects of growth temperature on performance and stability of zinc oxide thin film transistors fabricated by thermal atomic layer deposition. *Thin Solid Films*, **2014**, 562, 597-602	2.2	15
220	Thermoelectric properties of a doped LaNiO3 perovskite system prepared using a spark-plasma sintering process. *Electronic Materials Letters*, **2013**, 9, 513-516	2.9	7
219	Improved light emission through an AlGaN coalescence layer of 365-nm ultraviolet lighting-emitting diodes on patterned sapphire substrates. *Journal of the Korean Physical Society*, **2013**, 62, 942-948	0.6	
218	Ultraviolet light emitting diode based on p-NiO/n-ZnO nanowire heterojunction. *Journal of Crystal Growth*, **2013**, 370, 314-318	1.6	46
217	Influence of initial growth pressure on the optical properties of Si-doped nonpolar a-plane GaN grown with different doping levels. *Journal of Crystal Growth*, **2013**, 370, 22-25	1.6	2
216	Microstructural characterization and formation mechanism of 21□top facets of ZnO-based nanowall structures. *Physica B: Condensed Matter*, **2013**, 412, 12-16	2.8	3
215	Nonpolar a-GaN epilayers with reduced defect density using patterned r-plane sapphire substrates. *Thin Solid Films*, **2013**, 544, 244-248	2.2	6
214	Influence of growth temperature on the electrical and structural characteristics of conductive Al-doped ZnO thin films grown by atomic layer deposition. *Thin Solid Films*, **2013**, 545, 106-110	2.2	30
213	Controllable band-gap engineering of the ternary MgxNi1□O thin films deposited by radio frequency magnetron sputtering for deep ultra-violet optical devices. *Thin Solid Films*, **2013**, 529, 417-420	2.2	10
212	p-Channel oxide thin film transistors using solution-processed copper oxide. *ACS Applied Materials & Interfaces*, **2013**, 5, 2417-21	9.5	92
211	Two-step lateral growth of GaN for improved emission from blue light-emitting diodes. *Journal of Crystal Growth*, **2013**, 372, 157-162	1.6	1
210	Oxide p-n Heterojunction of Cu2O/ZnO Nanowires and Their Photovoltaic Performance. *Journal of Nanomaterials*, **2013**, 2013, 1-7	3.2	23
209	Semiconducting p-type MgNiO:Li epitaxial films fabricated by cosputtering method. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2013**, 31, 041501	2.9	2
208	Morphological evolution of silver nanoparticles and its effect on metal-induced chemical etching of silicon. *Journal of Nanoscience and Nanotechnology*, **2013**, 13, 3715-8	1.3	1
207	All-Solution-Processed InGaO3(ZnO)mThin Films with Layered Structure. *Journal of Nanomaterials*, **2013**, 2013, 1-6	3.2	5
206	An Optimization of Composition Ratio among Triple-Filled Atoms inIn0.3-x-yBaxCeyCo4Sb12System. *Journal of Nanomaterials*, **2013**, 2013, 1-7	3.2	2

205	Effects of channel thickness on electrical properties and stability of zinc tin oxide thin-film transistors. *Journal Physics D: Applied Physics*, **2013**, 46, 475106	3	25
204	Semitransparent all-oxide p-NiO/n-ZnO nanowire ultraviolet photosensors. *Journal of Materials Research*, **2013**, 28, 2605-2610	2.5	9
203	Effects of In or Ga doping on the growth behavior and optical properties of ZnO nanorods fabricated by hydrothermal process. *Physica Status Solidi (A) Applications and Materials Science*, **2013**, 210, 1552-1556	1.6	38
202	Artificial semiconductor/insulator superlattice channel structure for high-performance oxide thin-film transistors. *Scientific Reports*, **2013**, 3, 2737	4.9	61
201	Correlation between electrical properties and point defects in NiO thin films. *Metals and Materials International*, **2012**, 18, 1003-1007	2.4	12
200	Hybrid solution processed InGaO3(ZnO)m thin films with periodic layered structures and thermoelectric properties. *Journal of Materials Chemistry*, **2012**, 22, 16312		15
199	Classification of stacking faults and dislocations observed in nonpolar a-plane GaN epilayers using transmission electron microscopy. *Applied Surface Science*, **2012**, 258, 2522-2528	6.7	24
198	Effect of growth pressure on the morphology evolution and doping characteristics in nonpolar a-plane GaN. *Applied Surface Science*, **2012**, 258, 3565-3570	6.7	5
197	Effects of Al concentration on microstructural characteristics and electrical properties of Al-doped ZnO thin films on Si substrates by atomic layer deposition. *Journal of Nanoscience and Nanotechnology*, **2012**, 12, 5598-603	1.3	6
196	Biepitaxial Growth of High-Quality Semiconducting NiO Thin Films on (0001) Al2O3 Substrates: Microstructural Characterization and Electrical Properties. *Crystal Growth and Design*, **2012**, 12, 2495-2500	3.5	25
195	A stamped PEDOT:PSS-silicon nanowire hybrid solar cell. *Nanotechnology*, **2012**, 23, 145401	3.4	39
194	Transparent and flexible oxide thin-film-transistors using an aluminum oxide gate insulator grown at low temperature by atomic layer deposition. *Metals and Materials International*, **2012**, 18, 1055-1060	2.4	11
193	Remarkable increase of thermoelectric power factor using plasma treatment in layered InGaO3(ZnO)m thin films. *Surface and Interface Analysis*, **2012**, 44, 1519-1521	1.5	1
192	Irregular Electrical Conduction Types in Tin Oxide Thin Films Induced by Nanoscale Phase Separation. *Journal of the American Ceramic Society*, **2012**, 95, 324-327	3.8	34
191	Effect of Ti addition on the characteristics of titanium-zinc-tin-oxide thin-film transistors fabricated via a solution process. *Journal Physics D: Applied Physics*, **2012**, 45, 225103	3	11
190	Effect of annealing temperature on the electrical characteristics of Ti□n□n□ thin-film transistors fabricated via a solution process. *Journal of Materials Research*, **2012**, 27, 2293-2298	2.5	8
189	Tunable Electrical and Optical Properties in Composition Controlled Hf:ZnO Thin Films Grown by Atomic Layer Deposition. *Journal of the Electrochemical Society*, **2012**, 159, H384-H387	3.9	41
188	Donor and acceptor dynamics of phosphorous doped ZnO nanorods with stable p-type conduction: photoluminescence and junction characteristics. *Journal of Nanoscience and Nanotechnology*, **2012**, 12, 5571-6	1.3	1

187	Improved Electrical Stability in the Al Doped ZnO Thin-Film-Transistors Grown by Atomic Layer Deposition. *Journal of the Electrochemical Society*, **2011**, 158, H170	3.9	41
186	Highly selective spectral response with enhanced responsivity of n-ZnO/p-Si radial heterojunction nanowire photodiodes. *Applied Physics Letters*, **2011**, 98, 033102	3.4	83
185	Vertically arrayed Ga-doped ZnO nanorods grown by magnetron sputtering: The effect of Ga contents and microstructural evaluation. *Journal of Crystal Growth*, **2011**, 330, 17-21	1.6	20
184	Growth pressure dependence of optical and structural properties of a-plane InGaN/GaN multi-quantum wells on r-plane sapphire. *Journal of Crystal Growth*, **2011**, 339, 8-8	1.6	
183	Direct Formation of Transparent ITO Top Electrodes on High-Density ZnO Nanowires by Magnetron Sputtering. *Electrochemical and Solid-State Letters*, **2011**, 14, H446		9
182	Effect of Indium Mole Fraction on the Diode Characteristics of ZnO:In/p-Si(111) Heterojunctions. *Japanese Journal of Applied Physics*, **2011**, 50, 031101	1.4	1
181	Influence of synthesis temperature on the properties of Ga-doped ZnO nanorods grown by thermal evaporation. *Journal of Nanoscience and Nanotechnology*, **2011**, 11, 458-62	1.3	3
180	A facile method for morphological control of MgZnO nanostructures on GaAs substrates and their optical properties. *Journal of Nanoscience and Nanotechnology*, **2011**, 11, 7327-30	1.3	3
179	Ultralong ZnO nanowire arrays synthesized by hydrothermal method using repetitive refresh. *Journal of Nanoscience and Nanotechnology*, **2011**, 11, 7180-4	1.3	3
178	Fully transparent vertically aligned ZnO nanostructure-based ultraviolet photodetectors with high responsivity. *Sensors and Actuators B: Chemical*, **2011**, 160, 740-746	8.5	22
177	Over 95% of large-scale length uniformity in template-assisted electrodeposited nanowires by subzero-temperature electrodeposition. *Nanoscale Research Letters*, **2011**, 6, 467	5	19
176	Characterization of a-plane GaN layers grown on patterned r-sapphire substrate by metal organic chemical vapor deposition. *Current Applied Physics*, **2011**, 11, S90-S94	2.6	10
175	Drastic improvement of oxide thermoelectric performance using thermal and plasma treatments of the InGaZnO thin films grown by sputtering. *Acta Materialia*, **2011**, 59, 6743-6750	8.4	61
174	Control of the shell structure of ZnO/ZnS core-shell structure. *Journal of Nanoparticle Research*, **2011**, 13, 5825-5831	2.3	19
173	InGaN/GaN blue light emitting diodes using Al-doped ZnO grown by atomic layer deposition as a current spreading layer. *Journal of Crystal Growth*, **2011**, 326, 147-151	1.6	15
172	Effect of vicinal off-cut substrates on the basal stacking fault density in nonpolar a-GaN epilayers. *Journal of Crystal Growth*, **2011**, 328, 1-4	1.6	0
171	Density and aspect ratio controlled MgZnO nanowire arrays by spontaneous phase separation effect. *CrystEngComm*, **2011**, 13, 813-818	3.3	7
170	Tuning the morphology of copper nanowires by controlling the growth processes in electrodeposition. *Journal of Materials Chemistry*, **2011**, 21, 17967		28

169	Optical Properties of Ultrathin Copper Thin Films Sandwiched between Nb-Doped TiO2Films Studied with Spectroscopic Ellipsometry. *Japanese Journal of Applied Physics*, **2011**, 50, 055805	1.4	1
168	Electroluminescence enhancement of semipolar GaN light-emitting diodes grown on miscut m-plane sapphire substrates. *Current Applied Physics*, **2011**, 11, 954-958	2.6	16
167	Investigation of 2D/3D defects in controlled-growth oxygen-deficient ZnO nanowires and their field emission. *Chemical Physics Letters*, **2011**, 503, 266-271	2.5	5
166	Growth behavior and growth rate dependency in LEDs performance for Mg-doped a-plane GaN. *Journal of Crystal Growth*, **2011**, 326, 135-139	1.6	4
165	Electrical properties of GaN grown on a-plane GaN template by plasma-assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2011**, 324, 36-40	1.6	5
164	Effect of annealing temperature on the electrical performances of solution-processed InGaZnO thin film transistors. *Thin Solid Films*, **2011**, 519, 5146-5149	2.2	100
163	Role of the crystallinity of ZnO films in the electrical properties of bottom-gate thin film transistors. *Thin Solid Films*, **2011**, 519, 6801-6805	2.2	11
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